



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SA1417/2SC3647 — PNP / NPN Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Features

- Adoption of FBET, MBIT processes
- High breakdown voltage and large current capacity
- Fast switching speed
- Ultrasmall size making it easy to provide high-density small-sized hybrid ICs

Specifications () : 2SA1417

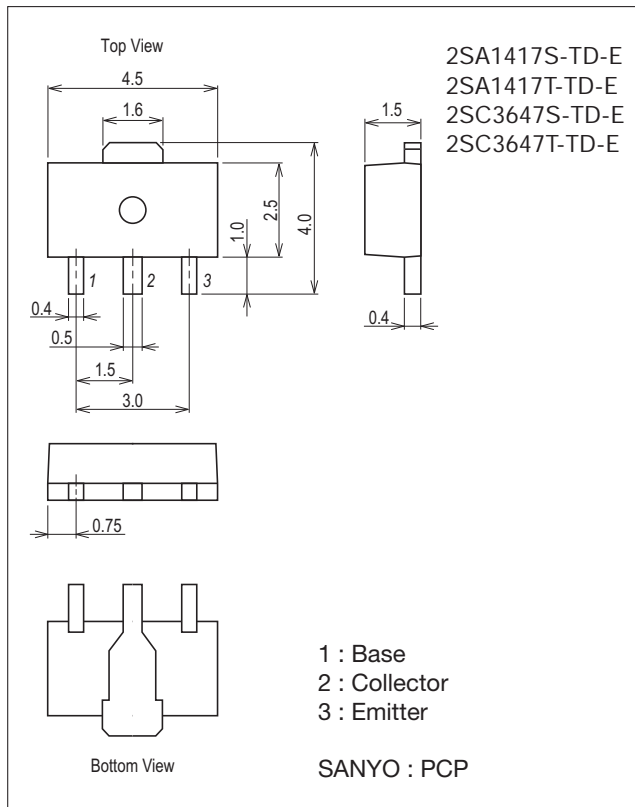
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)120	V
Collector-to-Emitter Voltage	VCEO		(-)100	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	IC		(-)2	A
Collector Current (Pulse)	ICP		(-)3	A
Collector Dissipation	PC		500	mW
		When mounted on ceramic substrate (250mm ² ×0.8mm)	1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ)

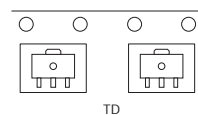
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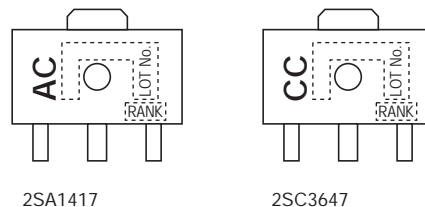
Product & Package Information

- Package : PCP
- JEITA, JEDEC : SC-62, SOT-89, TO-243
- Minimum Packing Quantity : 1,000 pcs./reel

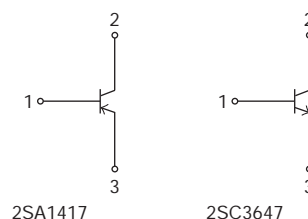
Packing Type: TD



Marking



Electrical Connection



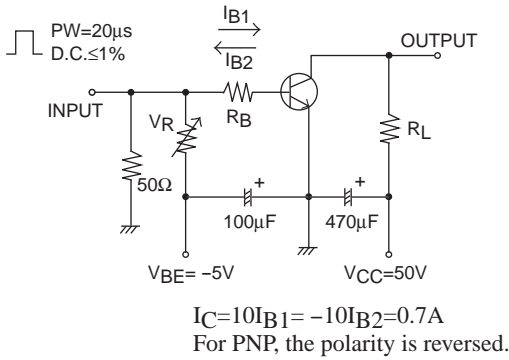
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V _{CB} =(-)100V, I _E =0A			(-)100	nA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0A			(-)100	nA
DC Current Gain	h _{FE}	V _{CE} =(-)5V, I _C =(-)100mA	100*		400*	
Gain-Bandwidth Product	f _T	V _{CE} =(-)10V, I _C =(-)100mA		120		MHz
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(25)16		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)1A, I _B =(-)100mA		(-0.22)0.13	(-0.6)0.4	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)1A, I _B =(-)100mA		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =(-)10μA, I _E =0A	(-)120			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =(-)1mA, R _{BE} =∞	(-)100			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0A	(-)6			V
Turn-On Time	t _{on}	See specified Test Circuit.		(80)80		ns
Storage Time	t _{stg}			(750)1000		ns
Fall Time	t _f			(40)50		ns

* : The 2SA1417 / 2S3647 are classified by 100mA h_{FE} as follows :

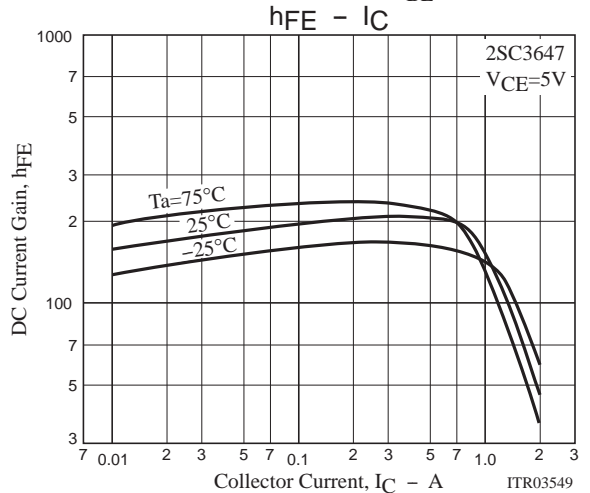
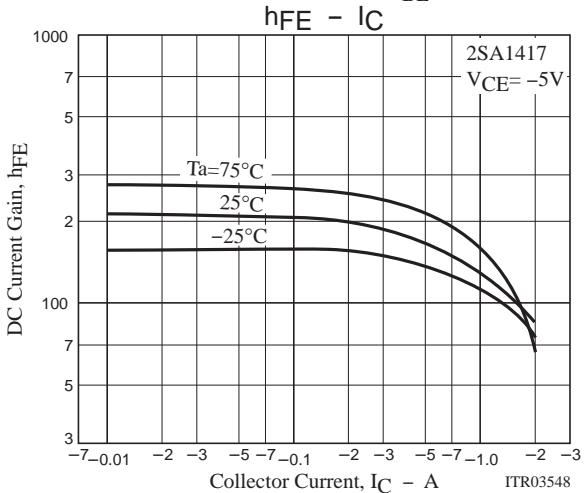
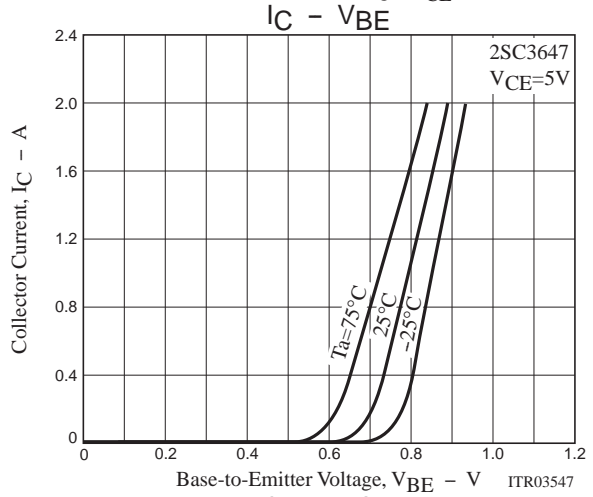
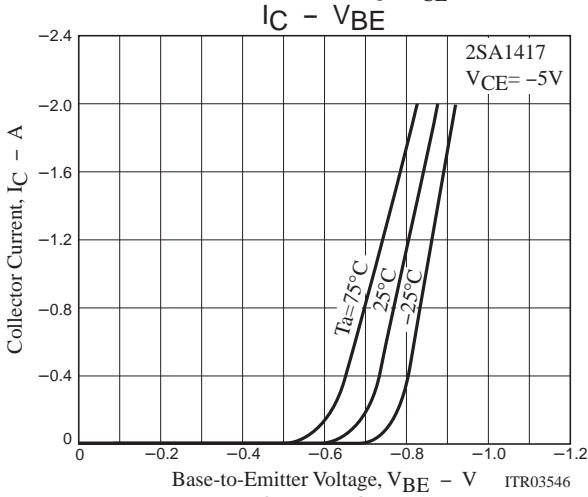
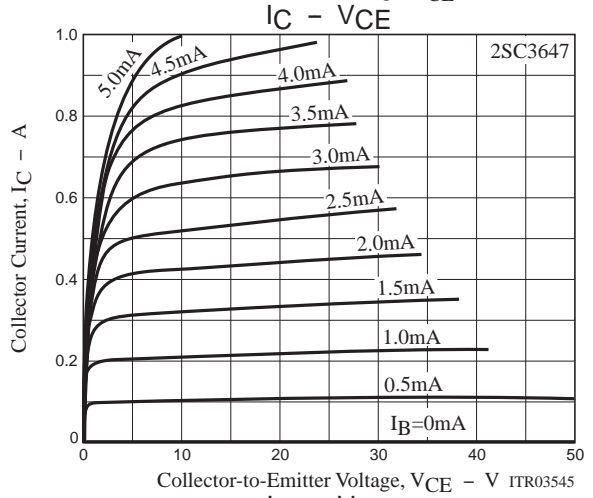
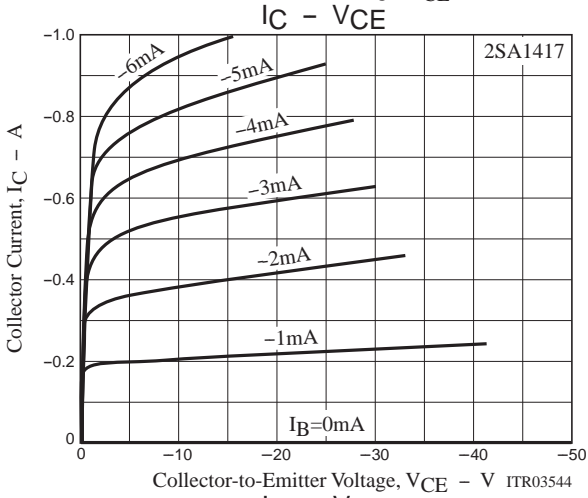
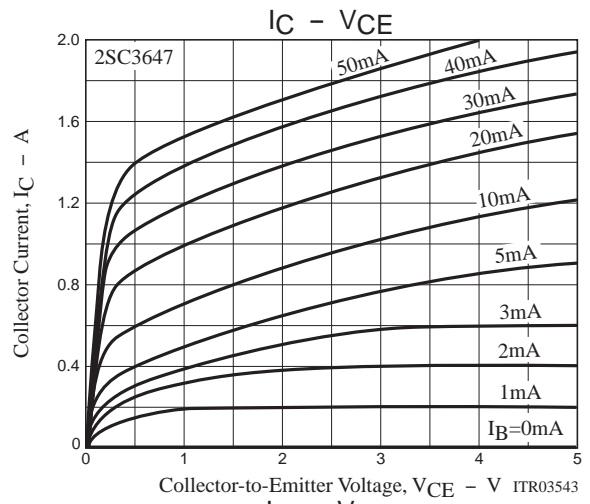
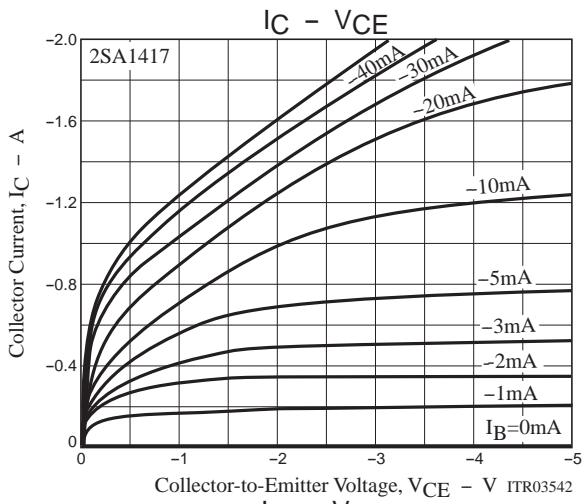
Rank	R	S	T
h _{FE}	100 to 200	140 to 280	200 to 400

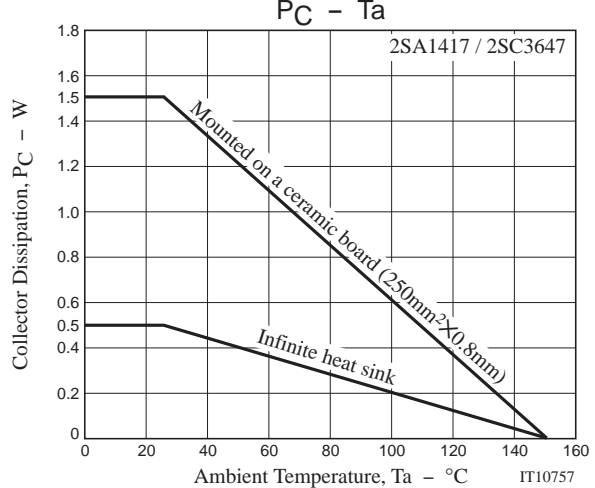
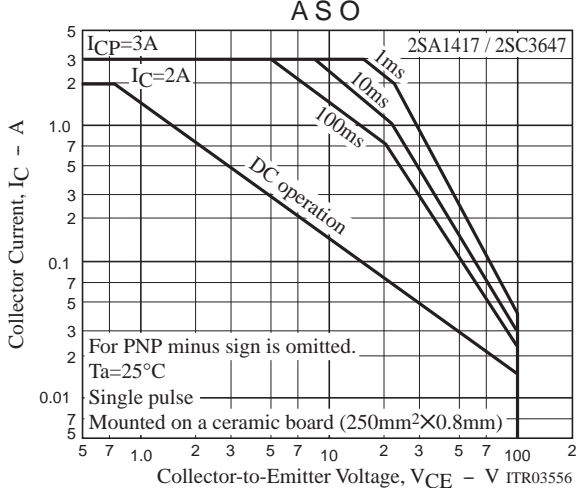
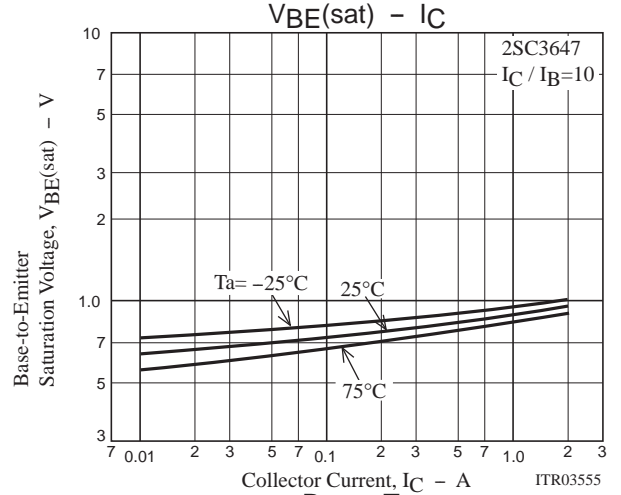
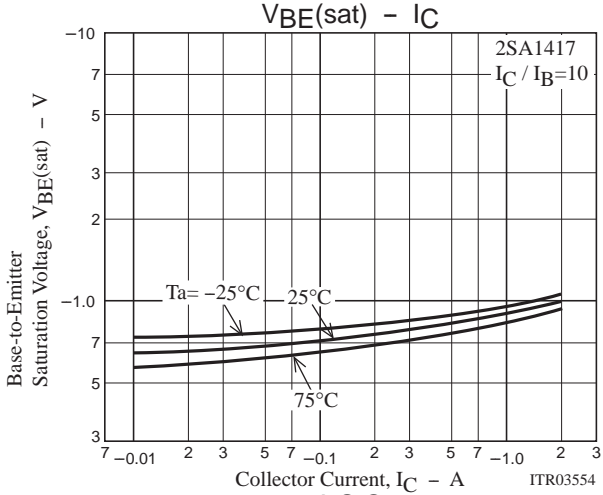
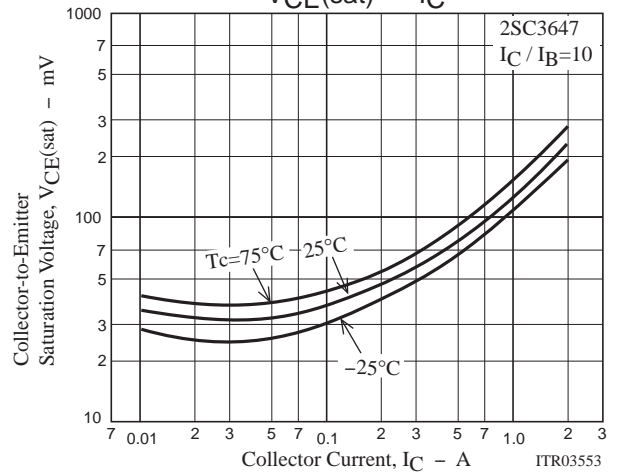
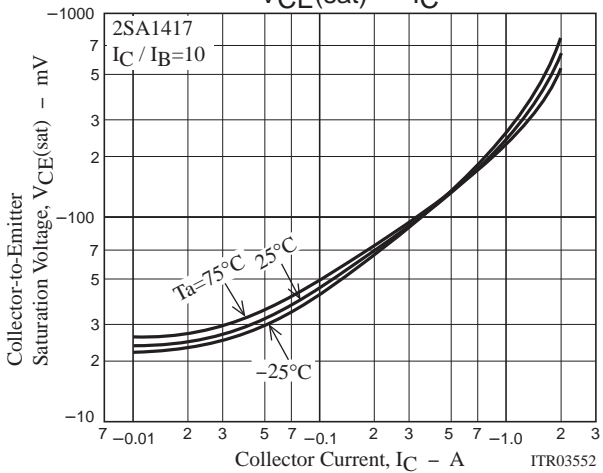
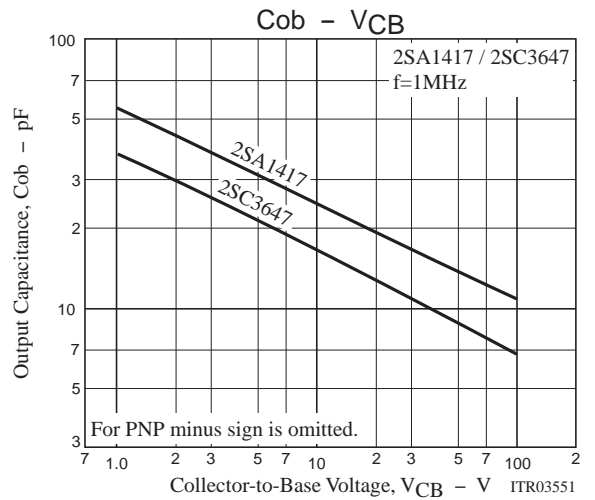
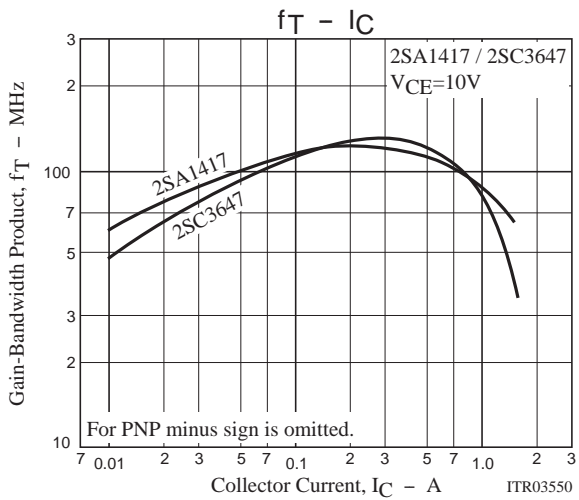
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SA1417S-TD-E	PCP	1,000pcs./reel	Pb Free
2SA1417T-TD-E	PCP	1,000pcs./reel	
2SC3647S-TD-E	PCP	1,000pcs./reel	
2SC3647T-TD-E	PCP	1,000pcs./reel	





Embossed Taping Specification

2SA1417S-TD-E, 2SA1417T-TD-E, 2SC3647S-TD-E, 2SC3647T-TD-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
PCP	PCP	1,000	4,000	24,000	4 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit :mm)

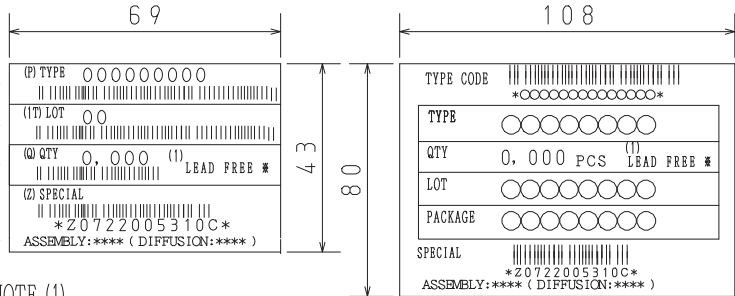
Outer box label
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Type No.
LOT No.
Quantity
Origin

Reel label



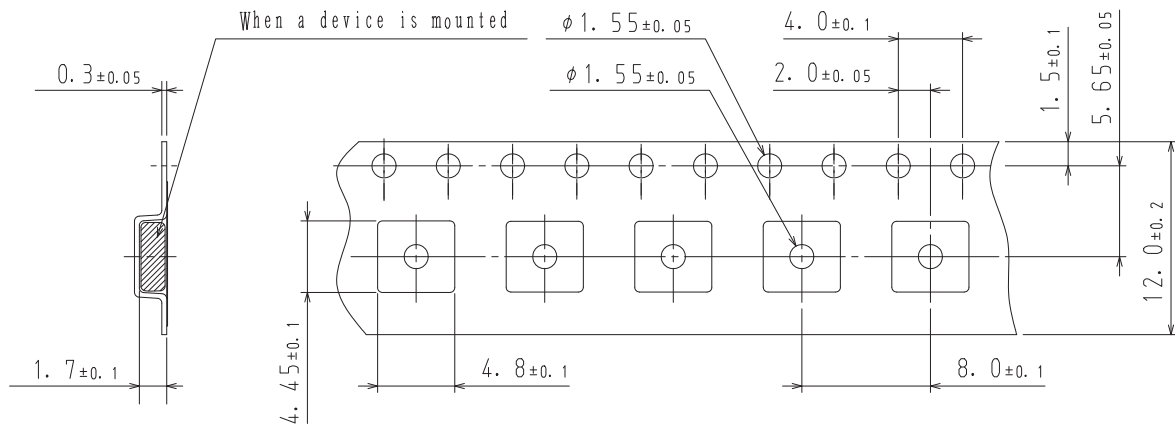
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

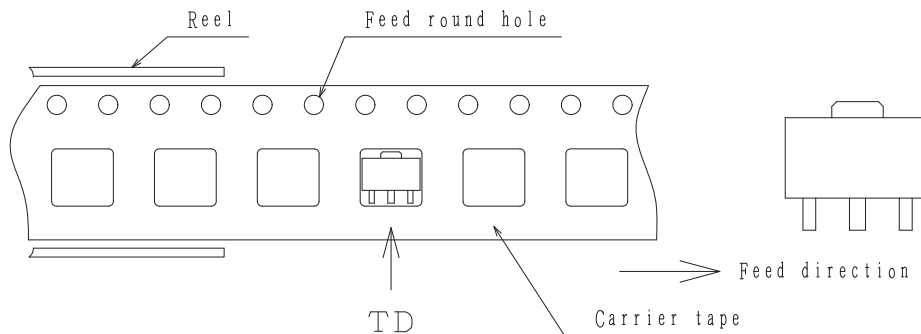
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



Those with pin 1 index on the feed hole side.....TD

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